林祐仲教授研究成果

(一)、近五年研究成果統計表

統計類別	2015		2016		2017		2018		2019	
	總篇數	IF 總和	總篇數	IF 總和	總篇數	IF 總和	總篇數	IF 總和	總篇數	IF 總和
SCI 期刊論文（限通訊作者）	21	41.728	14	28.907	11	21.602	12	19.034	6	10.078

統計類別	2020		以上合計	
	總篇數	IF 總和	總篇數	IF 總和
SCI 期刊論文（限通訊作者）	2	2.484	66	123.833

(二)、期刊論文：(*代表通訊作者)

[2020]

1. T. H. Su M. Y. Chen, W. S. Huang, and **Y. J. Lin***, 2020 February "Temperature-dependent resistive switching for gold/poly(methyl methacrylate)/heavily doped p-type Si/indium devices by incorporating black phosphorus into poly(methyl methacrylate)", ***Indian Journal of Physics*** (Accepted). (2018 IF: 1.242) (106-2112-M-018-001-MY3)
2. **Y. J. Lin*,** C. L. Wu, and H. C. Chang, 2020 January "Electrochemical properties and trap states of TiO_2 nanoparticles modified by doping with graphene and used as counter electrodes for dye-sensitized solar cell applications", ***Indian Journal of Physics*** Vol. 94, 47. (2018 IF: 1.242) (106-2112-M-018-001-MY3)

[2019]

3. J. F. Yu, **Y. J. Lin*,** M. H. Lin, and H. C. Chang, 2019 November "Incorporation of polyvinyl alcohol into ZrO_2 to modulate the hysteresis-type current-voltage characteristics of Au/ZrO_2/heavily doped p-type Si devices", ***Indian Journal of Physics*** (Accepted). (2018 IF: 1.242) (106-2112-M-018-001-MY3)
4. N. H. Yan, **Y. J. Lin*,** T. H. Su, and H. C. Chang, 2019 October "Optical

properties of and defects in ZnO nanorods that are modified by treatment with H_2O_2 and used as conductive filaments for poly(methyl methacrylate)-based resistive switching applications", ***Bulletin of Materials Science*** (Accepted). (2018 IF: 1.264) (106-2112-M-018-001-MY3)

5. **Y. J. Lin*,** C. C. Hung, J. S. Huang, S. Y. Lin, and H. C. Chang, 2019 October "Electrical and surface properties of SiO_2 films modified by ultraviolet irradiation and used as gate dielectrics for pentacene thin-film transistor applications", ***Chinese Journal of Physics*** Vol. 61, 248. (2018 IF: 2.544) (106-2112-M-018-001-MY3)
6. **Y. J. Lin*,** C. Y. Wu, and H. C. Chang, 2019 October "Ohmic-rectification conversion that is tuned using H_2O_2 for enhanced rectification and optoelectronic performance in MoS_2/ZnO nanorod devices", ***Chinese Journal of Physics*** Vol. 61, 22. (2018 IF: 2.544) (106-2112-M-018-001-MY3)
7. **Y. J. Lin*,** C. L. Wu, Z. Y. Ke, and H. C. Chang, 2019 September "Effects of graphene content on the resistive switching performance for Au/poly(methyl methacrylate):reduced graphene oxide/heavily doped p-type Si devices", ***Indian Journal of Physics*** (DOI: 10.1007/s12648-019-01568-7). (2018 IF: 1.242) (106-2112-M-018-001-MY3)
8. **Y. J. Lin*,** C. L. Wu, C. H. Chiang, and P. C. Kuo, 2019 June "Leakage conduction behavior for top- and bottom-contact pentacene thin film transistors", ***Indian Journal of Physics*** (DOI: 10.1007/s12648-019-01526-3). (2018 IF: 1.242) (106-2112-M-018-001-MY3)

[2018]

9. C. L. Wu and **Y. J. Lin*,** 2018 December "Incorporation of MoS_2 nanoflakes into poly(3-hexylthiophene)/n-type Si devices to improve the rectification behavior and optoelectronic performance", ***Indian Journal of Physics*** Vol. 92, 1533. (2018 IF: 1.242) (106-2112-M-018-001-MY3)
10. C. Y. Wu, **Y. J. Lin***, H. C. Chang, and Y. H. Chen, 2018 April "Effects of H_2O_2 treatment on the temperature-dependent behavior of carrier transport and the optoelectronic properties for sol–gel grown MoS_2/Si nanowire/Si devices", ***Journal of Materials Science: Materials in Electronics*** Vol. 29, 6032. (2018 IF: 2.195) (106-2112-M-018-001-MY3)
11. **Y. J. Lin*** and C. C. Hung**,** 2018 February "Temperature-dependent field-effect carrier mobility in organic thin-film transistors with a gate SiO_2 dielectric modified by H_2O_2 treatment", ***Applied Physics A*** Vol. 124, 173. (2018 IF: 1.784) (106-2112-M-018-001-MY3)

12. **Y. J. Lin*** and C. C. Hung, 2018 February "Temperature-dependent hole transport for pentacene thin-film transistor with a SiO_2 gate dielectric modified by $(NH_4)_2S_x$ treatment", ***Microelectronics Reliability*** Vol. 81, 90. (2018 IF: 1.483) (106-2112-M-018-001-MY3).
13. **Y. J. Lin***, G. M. Chang, H. C. Chang, and Y. H. Chen, 2018 February "Responsivity to solar irradiation and the response time of photodetectors that use ZnO nanoparticles with and without thermal annealing in pure oxygen ambient", ***Optik—International Journal for Light and Electron Optics*** Vol. 155, 157. (2018 IF: 1.914). (106-2112-M-018-001-MY3)
14. C. C. Hung and **Y. J. Lin***, 2018 January "Insertion of a pentacene layer into the gold/poly(methyl methacrylate)/heavily doped p-type Si/indium device leading to the modulation of resistive switching characteristics", ***Chemical Physics Letters*** Vol. 692, 388. (2018 IF: 1.901) (106-2112-M-018-001-MY3).
15. C. C. Hung and **Y. J. Lin***, 2018 January "Effects of $(NH_4)_2S_x$ treatment on the surface properties of SiO_2 as a gate dielectric for pentacene thin-film transistor applications", ***Materials Research Express*** Vol. 5, 015101. (2018 IF: 1.449) (106-2112-M-018-001-MY3).
16. **Y. J. Lin***, H. Z. Lin, H. C. Chang, and Y. H. Chen, 2018 January "Behavior of carrier transports and responsivity to solar irradiation for poly(3-hexylthiophene)/silicon devices with and without the insertion of silicon nanowires and the addition of black phosphorus", ***Thin Solid Films*** Vol. 646, 112. (2018 IF: 1.888) (106-2112-M-018-001-MY3)
17. C. C. Hung and **Y. J. Lin***, 2018 January "Surface properties of SiO_2 with and without H_2O_2 treatment as gate dielectrics for pentacene thin-film transistor applications", ***Chemical Physics Letters*** Vol. 691, 141. (2018 IF: 1.901) (106-2112-M-018-001-MY3).
18. S. M. Chen and **Y. J. Lin***, 2018 January "Controlled growth of MoS_2 nanopetals on the silicon nanowire array using the chemical vapor deposition method", ***Journal of Crystal Growth*** Vol. 481, 18. (2018 IF: 1.573) (106-2112-M-018-001-MY3)
19. T. H. Su, C. L. Wu, H. C. Chang, and **Y. J. Lin***, 2018 January "Electrical and optoelectronic properties for devices that use MoS_2 deposited on Si substrates with and without $(NH_4)_2S_x$ treatment by chemical vapor deposition", ***Journal of Materials Science: Materials in Electronics*** Vo. 29, 351. (2016 IF: 2.324) (103-2112-M-018-003-MY3 and 106-2112-M-018-001-MY3)
20. **Y. J. Lin***, G. M. Chang, and C. L. Wu, 2018 January "Effects of interface modification on electrical and optoelectronic properties of p-type $CuAlO_2$/n-type Si heterojunction devices", ***Journal of Materials Science: Materials in***

Electronics Vol. 29, 211. (2016 IF: 2.324) (106-2112-M-018-001-MY3)

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21. C. Y. Wu and **Y. J. Lin***, 2017 December "Responsivity to solar irradiation and the behavior of carrier transports for MoS_2/Si and MoS_2/Si nanowires/Si devices", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 18331. (2016 IF: 2.019) (103-2112-M-018-003-MY3 and 106-2112-M-018-001-MY3)
22. T. H. Su, C. H. Chiang, and **Y. J. Lin***, 2017 November "Temperature dependence of current-voltage characteristics of MoS_2/Si devices prepared by the chemical vapor deposition method", ***Microelectronics Reliability*** Vol. 78, 374. (2016 IF: 1.371) (103-2112-M-018-003-MY3 and 106-2112-M-018-001-MY3)
23. **Y. J. Lin***, T. H. Su, and S. M. Chen, 2017 October "Behavior of carrier transports and their sensitivity to solar irradiation for devices that use MoS_2 that is directly deposited on Si using the chemical vapor method", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 14430. (2016 IF: 2.019) (103-2112-M-018-003-MY3)
24. **Y. J. Lin*** and Z. Y. Ke, 2017 October "Resistive switching characteristics of devices having a trilayer $CuAlO_x$ structure in the dark and under visible light illumination", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 14377. (2016 IF: 2.019) (105-2815-C-018-032-E and 103-2112-M-018-003-MY3)
25. **Y. J. Lin***, Y. M. Chen, H. C. Chang, and Y. H. Chen, 2017 August "Solar-irradiation photodetectors based on ZnO nanoparticles with gold and indium electrodes", ***Optik—International Journal for Light and Electron Optics*** Vol. 142, 61. (2016 IF: 0.835). (100-2112-M-018-003-MY3 and 103-2112-M-018-003-MY3)
26. **Y. J. Lin*** and Y. M. Chen, 2017 July "Effects of Al doping on the responsivity of solar irradiation of devices that use ZnO nanoparticles", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 10205. (2016 IF: 2.019) (100-2112-M-018-003-MY3)
27. **Y. J. Lin*** and T. H. Su, 2017 July "SiO_2 substrate passivation effects on the temperature-dependent electrical properties of MoS_2 prepared by the chemical vapor deposition method", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 10106. (2016 IF: 2.019) (103-2112-M-018-003-MY3)
28. **Y. J. Lin***, 2017 June "Responsivity of In/ZnO nanoparticles/In and In/$Ti_{0.05}Zn_{0.95}O$ nanoparticles/In devices to solar irradiation", ***Sensors and Actuators: A. Physical*** Vol. 260, 62. (2016 IF: 2.499) (100-2112-M-018-003-MY3 and 103-2112-M-018-003-MY3)

29. Z. Y. Ke, H. C. Hung, and **Y. J. Lin***, 2017 March "Effects of surface modification of MoS_2:TiO_2:Pt counter electrodes by argon plasma treatment on photovoltaic performance of dye-sensitized solar cells", ***Journal of Materials Science: Materials in Electronics*** Vol. 28, 4908. (2016 IF: 2.019) (103-2112-M-018-003-MY3)
30. **Y. J. Lin***, Y. M. Chin, and H. C. Chang, 2017 January "Dependence of carrier transport of [6,6]-phenyl C61-butyric acid methyl ester/p-type Si diodes upon incorporation of ZnO nanoparticles", ***ECS Journal of Solid State Science and Technology*** Vol. 6, M5. (2018 IF: 1.795) (100-2112-M-018-003-MY3 and 103-2112-M-018-003-MY3)
31. **Y. J. Lin*** and Y. J. Chu, 2017 January "Oxygen vacancy and film crystallization effects on resistive switching behaviors of $CuAlO_x$ thin films", ***Journal of Alloys and Compounds*** Vol. 691, 263. (2018 IF: 4.175) (103-2112-M-018-003-MY3)

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32. **Y. J. Lin***, H. Z. Lin, Z. H. Tang, and H. C. Chang, 2016 December "Electrical and optoelectronic properties of [6,6]-phenyl C61-butyric acid methyl ester:Black phosphorus/p-type Si devices", ***Microelectronic Engineering*** Vol. 166, 5. (2018 IF: 1.654) (103-2112-M-018-003-MY3)
33. **Y. J. Lin***, H. Z. Lin, N. H. Yan, Z. H. Tang, and H. C. Chang**,** 2016 November "Incorporation of black phosphorus into P3HT:PCBM/n-type Si devices resulting in improvement in electrical and optoelectronic performances", ***Applied Physics A*** Vol. 122, 974. (2016 IF: 1.455) (103-2112-M-018-003-MY3)
34. **Y. J. Lin***, J. Y. Lee, and S. M. Chen, 2016 November "Changing electrical properties of PEDOT:PSS by incorporating with dimethyl sulfoxide" ***Chemical Physics Letters*** Vol. 664, 213. (2016 IF: 1.815) (103-2112-M-018-003-MY3)
35. **Y. J. Lin*** and T. H. Su, 2016 November "Interface modification of MoS_2/SiO_2 leading to conversion of conduction type of MoS_2", ***Applied Surface Science*** Vol. 387, 661. (2018 IF: 5.155) (103-2112-M-018-003-MY3)
36. H. Z. Lin and **Y. J. Lin***, 2016 October "Electrical conduction mechanisms in the temperature-dependent current-voltage characteristics of poly(3-hexylthiophene)/n-type Si devices", ***Microelectronics Reliability*** Vol. 65, 60. (2016 IF: 1.371) (103-2112-M-018-003-MY3)
37. H. Z. Lin and **Y. J. Lin***, 2016 October "Incorporation of black phosphorus into poly(3-hexylthiophene)/n-type Si devices resulting improvement in rectifying and optoelectronic performances", ***Synthetic Metals*** Vol. 220, 538. (2016 IF: 2.435) (103-2112-M-018-003-MY3)
38. **Y. J. Lin*** and Y. J. Chu, 2016 August "Temperature-dependent resistive

switching characteristics for Au/n-type $CuAlO_x$/heavily doped p-type Si devices", ***Microelectronics Reliability*** Vol. 63, 31. (2016 IF: 1.371) (103-2112-M-018-003-MY3)

39. H. C. Hung, **Y. J. Lin***, and Z. Y. Ke, 2016 May "Interface modification of MoS_2:TiO_2 counter electrode/electrolyte in dye-sensitized solar cells by doping with different Co contents", ***Journal of Materials Science: Materials in Electronics*** Vol. 27, 5059. (2016 IF: 2.019) (103-2112-M-018-003-MY3)
40. **Y. J. Lin*** and W. S. Ni, 2016 April "Effects of sulfide treatment on the electrical, photoluminescent and structural properties of ZnS films", ***Journal of Luminescence*** Vol. 172, 286. (2016 IF: 2.686) (103-2112-M-018-003-MY3)
41. J. Luo and **Y. J. Lin***, 2016 March "Point defect-induced magnetic properties in $CuAlO_2$ films without magnetic impurities", ***Applied Physics A*** Vol. 122, 163. (2016 IF: 1.455) (103-2112-M-018-003-MY3 and 100-2112-M-018-003-MY3)
42. **Y. J. Lin***, C. C. Hung, J. J. Zeng, and H. C. Chang, 2016 February "Extrinsic and intrinsic performance effects on the electrical property in few-layer graphene", ***Applied Physics A*** Vol. 122, 83. (2016 IF: 1.455) (103-2112-M-018-003-MY3)
43. J. Y. Lee and **Y. J. Lin***, 2016 February "Effect of incorporation of black phosphorus into PEDOT:PSS on conductivity and electron-phonon coupling" ***Synthetic Metals*** Vol. 212, 180. (2016 IF: 2.435) (103-2112-M-018-003-MY3)
44. T. H. Su and **Y. J. Lin***, 2016 January "Effects of nitrogen plasma treatment on the electrical property and band structure of few-layer MoS_2", ***Applied Physics Letters*** Vo. 108, 033103. (2016 IF: 3.411) (103-2112-M-018-003-MY3)
45. **Y. J. Lin*** and H. Y. Tsao, 2016 January "Ambient-atmosphere annealing effect on the carrier conduction behavior based on the linear-regime transfer characteristics of pentacene thin film transistors", ***Microelectronic Engineering*** Vol. 149, 57. (2016 IF: 1.806) (103-2112-M-018-003-MY3 and 100-2112-M-018-003-MY3)

[2015]

46. **Y. J. Lin***, W. S. Ni, and J. Y. Lee, 2015 December "Erratum: "Effect of incorporation of ethylene glycol into PEDOT:PSS on electron phonon coupling and conductivity" [J. Appl. Phys. 117, 215501 (2015)]", ***Journal of Applied Physics*** Vol. 118, 219901. (2014 IF: 2.183) (103-2112-M-018-003-MY3)
47. **Y. J. Lin***, 2015 December "Correlation between phonon and impurity scatterings, potential fluctuations and leakage conduction of graphene/n-type Si Schottky diodes", ***Superlattices and Microstructures*** Vol. 88, 645. (2014 IF: 2.097) (103-2112-M-018-003-MY3)
48. W. S. Ni, **Y. J. Lin***, H. C. Chang, C. J. Liu, and L. R. Chen, 2015 December

"Luminescence behavior and compensation effect on the hole concentration in the sol-gel $Zn_{1-x}Cu_xS_y$ films with different compositions", ***Journal of Luminescence*** Vol. 168, 241. (2014 IF: 2.719) (103-2112-M-018-003-MY3)

49. W. S. Ni and **Y. J. Lin***, 2015 November "Defect-induced magnetic properties of Cu-doped ZnS films with different copper contents", ***Journal of Alloys and Compounds*** Vol. 649, 968. (2014 IF: 2.999) (103-2112-M-018-003-MY3)
50. **Y. J. Lin***, C. H. Ruan, Y. J. Chu, C. J. Liu, and F. H. Lin, 2015 October "Correlation between interface modification and rectifying behavior of p-type Cu_2ZnSnS_4/n-type Si diodes", ***Applied Physics A*** Vol. 121, 103. (2014 IF: 1.704) (103-2112-M-018-003-MY3)
51. **Y. J. Lin*** and J. F. Yu, 2015 October "Photoluminescent, morphological and electrical properties of ZrO_2 and ZrO_2:polyvinyl alcohol composite thin films", ***Journal of Non-Crystalline Solids*** Vol. 426, 132. (2014 IF: 1.766). (103-2112-M-018-003-MY3)
52. W. H. Jhang and **Y. J. Lin***, 2015 August "Interface modification of MoS_2 counter electrode/electrolyte in dye-sensitized solar cells by incorporating TiO_2 nanoparticles", ***Current Applied Physics*** Vol. 15, 906. (2014 IF: 2.212) (103-2112-M-018-003-MY3)
53. **Y. J. Lin*** and C. F. You, 2015 July "Defect-dependent carrier transport behavior of polymer:ZnO composites/electrodeposited CdS/indium tin oxide devices", ***Journal of Applied Physics*** Vol. 118, 044503. (2014 IF: 2.183) (103-2112-M-018-003-MY3)
54. J. H. Lin and **Y. J. Lin***, 2015 July "Cadmium content-dependent photoluminescent properties and band offsets of $Zn_{1-x}Cd_xO$ films", ***Journal of Materials Science: Materials in Electronics*** Vol. 26, 5254. (2014 IF: 1.569) (103-2112-M-018-003-MY3)
55. **Y. J. Lin***, W. S. Ni, and J. Y. Lee, 2015 June "Effect of incorporation of ethylene glycol into PEDOT:PSS on electron phonon coupling and conductivity", ***Journal of Applied Physics*** Vol. 117, 215501. (2014 IF: 2.183) (103-2112-M-018-003-MY3)
56. W. H. Jhang and **Y. J. Lin***, 2015 June "Overpotential modification at the MoS_2 counter electrode/electrolyte interfaces by thermal annealing resulting improvement in photovoltaic performance of dye-sensitized solar cells", ***Journal of Materials Science: Materials in Electronics*** Vol. 26, 3739. (2014 IF: 1.569) (103-2112-M-018-003-MY3)
57. W. S. Ni and **Y. J. Lin***, 2015 June "Conduction behavior conversion for Cu-doped ZnS/n-type Si devices with different Cu contents", ***Applied Physics A*** Vol. 119, 1127. (2014 IF: 1.704) (103-2112-M-018-003-MY3)

58. C. L. Tsai, **Y. J. Lin***, and J. H. Lin, 2015 May "Interface characteristics for graphene contact to n-type and p-type GaN observed by X-ray photoelectron spectroscopy", ***Journal of Materials Science: Materials in Electronics*** Vol. 26, 3052. (2014 IF: 1.569) (103-2112-M-018-003-MY3)
59. **Y. J. Lin***, H. Y. Tsao, and D. S. Liu, 2015 April "Dielectric substrate effect on the temperature-dependent electrical properties of pentacene films", ***Journal of Materials Science: Materials in Electronics*** Vol. 26, 2579. (2014 IF: 1.569) (103-2112-M-018-003-MY3 and 100-2112-M-018-003-MY3)
60. **Y. J. Lin***, Y. M. Chin, and H. C. Chang, 2015 April "Environmental effects on temperature-dependent carrier transports in poly(3-hexylthiophene) films", ***Applied Physics A*** Vol. 119, 365. (2014 IF: 1.704) (103-2112-M-018-003-MY3)
61. C. H. Ruan, **Y. J. Lin***, Y. H. Chen, and H. C. Chang, 2015 April "Rectifying performance of p-type tin(II) sulfide contacts on n-type silicon: Effect of silicon nanowire sulfidation on electronic transport of heterojunction diodes", ***Materials Science in Semiconductor Processing*** Vol. 32, 62. (2014 IF: 1.955) (103-2112-M-018-003-MY3)
62. **Y. J. Lin***, H. C. Chang, and D. S. Liu, 2015 March "Tuning charge transport in pentacene thin film transistors using the strain-induced electron-phonon coupling modification", ***Applied Physics A*** Vol. 118, 1205. (2014 IF: 1.704) (103-2112-M-018-003-MY3)
63. **Y. J. Lin***, W. M. Cho, H. C. Chang, and Y. H. Chen, 2015 March "Interface modification and trap-type transformation in Al-doped CdO/Si-nanowire arrays/p-type Si devices by nanowire surface passivation", ***Current Applied Physics*** Vol. 15, 213. (2014 IF: 2.212) (103-2112-M-018-003-MY3 and 100-2112-M-018-003-MY3)
64. **Y. J. Lin***, C. F. You, H. C. Chang, C. J. Liu, and C. A. Wu, 2015 February "Effects of sulfide treatment on the photoluminescent and structural properties of electrodeposited CdS films, ***Journal of Luminescence*** Vol. 158, 407. (2014 IF: 2.719) (100-2112-M-018-003-MY3 and 103-2112-M-018-003-MY3)
65. J. H. Lin, **Y. J. Lin***, and H. C. Chang, 2015 January "Tuning electrical parameters of graphene/p-type polycrystalline silicon Schottky diodes by ultraviolet irradiation", ***Applied Physics A*** Vol. 118, 361. (2014 IF: 1.704) (102-2120-M-194-002 and 103-2112-M-018-003-MY3)
66. **Y. J. Lin***, J. J. Zeng, and H. C. Chang, 2015 January "Temperature-dependent electrical properties for graphene Schottky contact on n-type Si with and without sulfide treatment", ***Applied Physics A*** Vol. 118, 353. (2014 IF: 1.704) (103-2112-M-018-003-MY3)

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67. **Y. J. Lin*** and J. J. Zeng, 2014 December "Determination of Schottky barrier heights and Fermi-level unpinning at the graphene/n-type Si interfaces by X-ray photoelectron spectroscopy and Kelvin probe", ***Applied Surface Science*** Vol. 322, 225. (2013 IF: 2.538) (103-2112-M-018-003-MY3)
68. **Y. J. Lin*** and Y. M. Chin, 2014 November "Correlation between the electron-phonon coupling and rectifying performance for poly(3-hexylthiophene)/n-type Si devices", ***Journal of Applied Physics*** Vol. 116, 173709. (2013 IF: 2.185) (103-2112-M-018-003-MY3)
69. **Y. J. Lin***, H. Y. Tsao, and D. S. Liu, 2014 November "Effects of a metallic front gate on the temperature-dependent electronic property of pentacene films", ***Materials Chemistry and Physics*** Vol. 148, 431. (2013 IF: 2.129) (103-2112-M-018-003-MY3)
70. **Y. J. Lin*** and Y. C. Lin, 2014 October "Temperature-dependent gate-swing hysteresis of pentacene thin film transistors", ***AIP Advances*** Vol. 4, 107105. (2013 IF: 1.590) (103-2815-C-018-017-M)
71. **Y. J. Lin***, Y. M. Chin, C. Y. Wu, and D. S. Liu, 2014 September "Electron-phonon coupling modification and carrier mobility enhancement in poly(3,4-ethylenedioxythiophene) doped with poly(4-styrenesulfonate) films by ultraviolet irradiation", ***Journal of Applied Physics*** Vol. 116, 093707. (2013 IF: 2.185) (103-2112-M-018-003- MY3)
72. J. J. Zeng and **Y. J. Lin***, 2014 August "Electrical and optoelectronic properties of graphene Schottky contact on Si-nanowire arrays with and without H_2O_2 treatment", ***Applied Physics A*** Vol. 116, 581. (2013 IF: 1.694) (100-2112-M-018-003-MY3)
73. **Y. J. Lin*** and Y. C. Lin, 2014 July "Electrical conduction mechanisms in transfer characteristics of pentacene thin film transistors", ***Applied Physics Letters*** Vol. 105, 023506. (2013 IF: 3.515) (103-2815-C-018-017-M)
74. **Y. J. Lin*** and S. H. Yang, 2014 July "Carrier transport and photoresponse for heterojunction diodes based on the reduced graphene oxide-based TiO_2 composite and p-type Si", ***Applied Physics A*** Vol. 116, 91. (2013 IF: 1.694) (100-2112-M-018-003-MY3)
75. **Y. J. Lin*** and J. H. Lin, 2014 June "Annealing effect on Schottky barrier inhomogeneity of graphene/n-type Si Schottky diodes", ***Applied Surface Science*** Vol. 311, 224. (2013 IF: 2.538) (100-2112-M-018-003-MY3)
76. J. J. Zeng and **Y. J. Lin***, 2014 June "Tuning the work function of graphene by nitrogen plasma treatment with different radio-frequency powers", ***Applied Physics Letters*** Vol. 104, 233103. (2013 IF: 3.515) (100-2112-M-018-003-MY3)
77. T. H. Su and **Y. J. Lin***, 2014 April "Electrical conduction mechanisms of

Au/NiO/heavily doped p-type Si memory devices", ***Applied Physics Letters*** Vol. 104, 153504. (2013 IF: 3.515) (100-2112-M-018-003-MY3)

78. J. J. Zeng and **Y. J. Lin***, 2014 April "Schottky barrier inhomogeneity for graphene/Si-nanowire arrays/n-type Si Schottky diodes", ***Applied Physics Letters*** Vol. 104, 133506. (2013 IF: 3.515) (100-2112-M-018-003-MY3)
79. J. J. Zeng and **Y. J. Lin***, 2014 May "Effects of sulfide treatment on electronic transport of graphene/n-type Si Schottky diodes", ***Materials Chemistry and Physics*** Vol. 145, 250. (2013 IF: 2.129) (100-2112-M-018-003-MY3)
80. Y. M. Chin and **Y. J. Lin***, 2014 May "Effects of H_2O_2 treatment on the optoelectronic property of poly(3-hexylthiophene) doped with the reduced graphene oxide sheets/Si-nanowire arrays/n-type Si diodes", ***Materials Chemistry and Physics*** Vol. 145, 232. (2013 IF: 2.129) (100-2112-M-018-003-MY3)
81. H. Y. Tsao and **Y. J. Lin***, 2014 Feb. "Resistive switching behaviors of Au/pentacene/Si-nanowire arrays/heavily doped n-type Si devices for memory applications", ***Applied Physics Letters*** Vol. 104, 053501. (2013 IF: 3.515) (100-2112-M-018-003-MY3)
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